

## ABSTRACT

A group III nitride crystal having a small dislocation density and good quality and a production method for the group III nitride crystal are provided.

5 The production method for the group III nitride crystal is characterized by growing a group III nitride crystal film 2 on a substrate 1, depositing a metallic film 3 thereon and, then, not only changing the metallic film 3 into a metallic nitride film 4 and, further, generating a pore 4h, but also forming a void portion 2b in the group III nitride crystal film 2 by performing a thermal treatment and, 10 thereafter, filling the void portion 2b by a group III nitride crystal 5 for filling by further growing a group III nitride crystal and, subsequently, growing a group III nitride crystal 6 on the metallic nitride film 4.